# -3.3 V / -5 V Differential ECL to +3.3 V LVTTL Translator

### Description

The MC100EPT25 is a Differential ECL to LVTTL translator. This device requires +3.3 V, -3.3 V to -5.2 V, and ground. The small outline 8-lead package and the single gate of the EPT25 make it ideal for applications which require the translation of a clock or data signal.

The  $V_{BB}$  output allows the EPT25 to also be used in a single-ended input mode. In this mode the  $V_{BB}$  output is tied to the D input for a inverting buffer or the  $\overline{D}$  input for a non-inverting buffer. If used, the  $V_{BB}$  pin should be bypassed to ground with at least a 0.01  $\mu F$  capacitor.

#### **Features**

- 1.1 ns Typical Propagation Delay
- Maximum Frequency > 275 MHz Typical
- Operating Range:
  - $V_{CC} = 3.0 \text{ V}$  to 3.6 V;  $V_{EE} = -5.5 \text{ V}$  to -3.0 V; GND = 0 V
- 24 mA TTL Outputs
- Q Output Will Default LOW with Inputs Open or at V<sub>EE</sub>
- V<sub>BB</sub> Output
- Open Input Default State
- Safety Clamp on Inputs
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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SOIC-8 NB D SUFFIX CASE 751-07 TSSOP-8 DT SUFFIX CASE 948R-02

DFN-8 MN SUFFIX CASE 506AA

#### **MARKING DIAGRAMS\***







A = Assembly Location

= Wafer Lot

Y = Year

W = Work Week

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)
\*For additional marking information, refer to Application Note AND8002/D.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC100EPT25DG	SOIC-8 NB (Pb-Free)	98 Units/Tube
MC100EPT25DR2G	SOIC-8 NB (Pb-Free)	2500/Tape & Reel
MC100EPT25DTG	TSSOP-8 (Pb-Free)	100 Units/Tube
MC100EPT25DTR2G	TSSOP-8 (Pb-Free)	2500/Tape & Reel
MC100EPT25MNR4G	DFN-8 (Pb-Free)	1000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

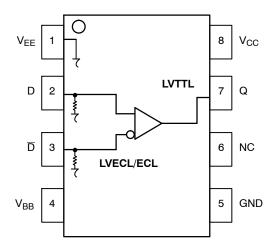


Figure 1. 8-Lead Pinout (Top View) and Logic Diagram

**Table 1. PIN DESCRIPTION** 

PIN	FUNCTION			
Q	LVTTL Output			
D*, <del>D</del> *	Differential ECL Input Pair			
V <sub>CC</sub>	Positive Supply			
$V_{BB}$	Output Reference Voltage			
GND	Ground			
V <sub>EE</sub>	Negative Supply			
NC	No Connect			
EP	(DFN8 only) Thermal exposed pad must be connected to a sufficient thermal conduit. Electrically connect to the most negative supply (GND) or leave unconnected, floating open.			

<sup>\*</sup> Pins will default LOW when left open.

**Table 2. ATTRIBUTES** 

Characteristics	Value
Internal Input Pulldown Resistor	75 kΩ
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model Machine Model Charged Device Model	> 4 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 NB TSSOP-8 DFN-8	Level 1 Level 3 Level 1
Flammability Rating Oxygen Index: 28 to 34	UL-94 V-0 @ 0.125 in
Transistor Count	111 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	

<sup>1.</sup> For additional information, see Application Note AND8003/D.

**Table 3. MAXIMUM RATINGS** 

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V <sub>CC</sub>	Positive Power Supply	GND = 0 V	V <sub>EE</sub> = -5.0 V	3.8	V
V <sub>EE</sub>	Negative Power Supply	GND = 0 V	V <sub>CC</sub> = +3.3 V	-6	V
V <sub>IN</sub>	Input Voltage	GND = 0 V		0 to V <sub>EE</sub>	V
I <sub>BB</sub>	V <sub>BB</sub> Sink/Source			± 0.5	mA
T <sub>A</sub>	Operating Temperature Range			-40 to +85	°C
T <sub>stg</sub>	Storage Temperature Range			-65 to +150	°C
$\theta_{JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 NB	190 130	°C/W
θJC	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
$\theta_{\sf JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8	185 140	°C/W
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44	°C/W
$\theta_{JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	DFN-8	129 84	°C/W
T <sub>sol</sub>	Wave Solder (Pb-Free)	<2 to 3 sec @ 260°C		265	°C
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	(Note 1)	DFN-8	35 to 40	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 4. NECL DC CHARACTERISTICS ( $V_{CC} = 3.3 \text{ V}$ ;  $V_{EE} = -5.5 \text{ V}$  to -3.0 V; GND = 0.0 V (Note 1))

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
IEE	Power Supply Current	8.0	16	25	8.0	16	25	8.0	16	25	mA
V <sub>IH</sub>	Input HIGH Voltage Single-Ended	-1225		-880	-1225		-880	-1225		-880	mV
V <sub>IL</sub>	Input LOW Voltage Single-Ended	-1945		-1625	-1945		-1625	-1945		-1625	mV
V <sub>BB</sub>	Output Voltage Reference	-1525	-1425	-1325	-1525	-1425	-1325	-1525	-1425	-1325	mV
V <sub>IHCMR</sub>	Input HIGH Voltage Common Mode Range (Note 2)	V <sub>EE</sub> ·	+ 2.0	0.0	V <sub>EE</sub> .	+ 2.0	0.0	V <sub>EE</sub> -	+ 2.0	0.0	٧
I <sub>IH</sub>	Input HIGH Current			150			150			150	μΑ
I <sub>IL</sub>	Input LOW Current	0.5			0.5			0.5			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

<sup>1.</sup> JEDEC standard multilayer board - 2S2P (2 signal, 2 power)

<sup>1.</sup> Input parameters vary 1:1 with GND.

<sup>2.</sup>  $V_{IHCMR}$  min varies 1:1 with  $V_{EE}$ ,  $V_{IHCMR}$  max varies 1:1 with  $V_{CC}$ . The  $V_{IHCMR}$  range is referenced to the most positive side of the differential input signal.

 $\textbf{Table 5. TTL OUTPUT DC CHARACTERISTICS} \ (V_{CC} = 3.3 \ V; \ V_{EE} = -5.5 \ V \ to \ -3.0 \ V; \ GND = 0.0 \ V; \ T_A = \ -40 ^{\circ}C \ to \ 85 ^{\circ}C)$ 

Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V <sub>OH</sub>	Output HIGH Voltage	I <sub>OH</sub> = -3.0 mA	2.2			V
V <sub>OL</sub>	Output LOW Voltage	I <sub>OL</sub> = 24 mA			0.5	V
I <sub>CCH</sub>	Power Supply Current		6	10	14	mA
I <sub>CCL</sub>	Power Supply Current		7	12	17	mA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

Table 6. AC CHARACTERISTICS ( $V_{CC} = 3.0 \text{ V}$  to 3.6 V;  $V_{EE} = -5.5 \text{ V}$  to -3.0 V; GND = 0.0 V (Note 1))

		-40°C		25°C		85°C					
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f <sub>max</sub>	Maximum Frequency (See Figure 2 F <sub>max</sub> /JITTER)	275			275			275			MHz
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay to Output Differential (Cross-Point to 1.5 V)	500	950	1300	800	950	1600	800	960	1600	ps
t <sub>SKPP</sub>	Device-to-Device Skew (Note 2)			500			500			500	ps
tuitter	Random Clock Jitter (RMS) (See Figure 2 F <sub>max</sub> /JITTER)		0.2	< 1		0.2	< 1		0.2	< 1	ps
V <sub>PP</sub>	Input Voltage Swing (Differential)	150	800	1200	150	800	1200	150	800	1200	mV
t <sub>r</sub>	Output Rise/Fall Times $Q, \overline{Q}$ (0.8 V – 2.0 V)	300 900	474 1160	600 1400	300 900	459 1100	600 1400	300 900	457 1100	600 1400	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

- 1. Measured with a 750 mV 50% duty-cycle clock source.  $R_L$  = 500  $\Omega$  to GND and  $C_L$  = 20 pF to GND. Refer to Figure 3.
- 2. Skews are measured between outputs under identical conditions.

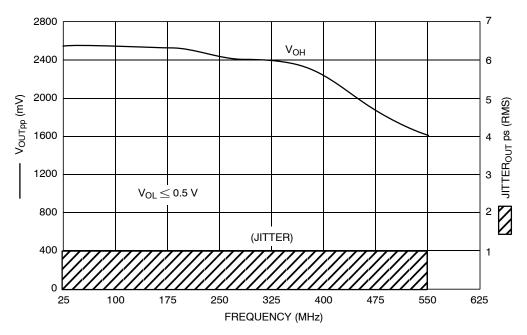


Figure 2. F<sub>max</sub>/Jitter

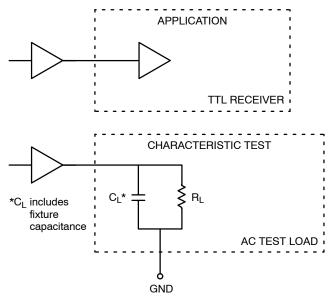


Figure 3. TTL Output Loading Used for Device Evaluation

## **Resource Reference of Application Notes**

AN1405/D - ECL Clock Distribution Techniques

AN1406/D - Designing with PECL (ECL at +5.0 V)

AN1503/D - ECLinPS™ I/O SPiCE Modeling Kit

AN1504/D - Metastability and the ECLinPS Family

AN1568/D - Interfacing Between LVDS and ECL

AN1672/D - The ECL Translator Guide

AND8001/D - Odd Number Counters Design

AND8002/D - Marking and Date Codes

AND8020/D - Termination of ECL Logic Devices

AND8066/D - Interfacing with ECLinPS

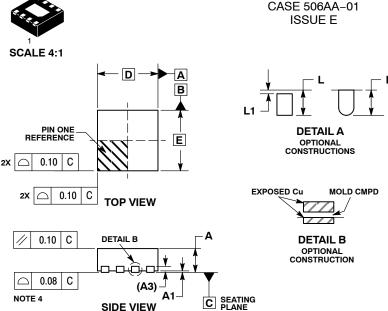
AND8090/D - AC Characteristics of ECL Devices

DETAIL A

е

- D2 →

**BOTTOM VIEW** 



0.10 C

Ф

AB

0.05 C NOTE 3

DFN8 2x2, 0.5P CASE 506AA-01

**DATE 22 JAN 2010** 

#### NOTES

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994 . CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN
- 0.15 AND 0.20 MM FROM TERMINAL TIP. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS					
DIM	MIN	MAX				
Α	0.80	1.00				
A1	0.00	0.05				
А3	0.20	REF				
b	0.20	0.30				
D	2.00	BSC				
D2	1.10	1.30				
E	2.00 BSC					
E2	0.70 0.90					
е	0.50 BSC					
K	0.30 REF					
L	0.25	0.35				
L1		0.10				

#### **GENERIC MARKING DIAGRAM\***

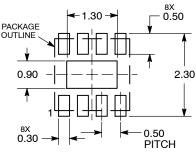


XX = Specific Device Code

= Date Code = Pb-Free Device

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

#### **RECOMMENDED SOLDERING FOOTPRINT\***



**DIMENSIONS: MILLIMETERS** 

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

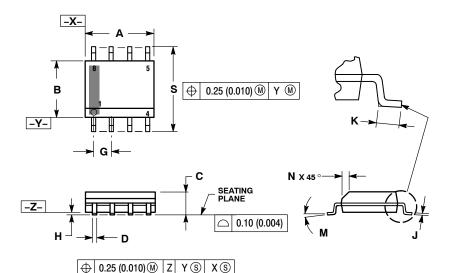
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DESCRIPTION:	DFN8, 2.0X2.0, 0.5MM PITO	CH	PAGE 1 OF 1		

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SOIC-8 NB CASE 751-07 **ISSUE AK** 

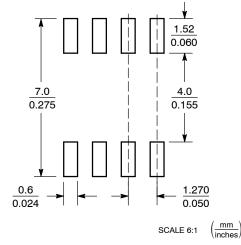
**DATE 16 FEB 2011** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	7 BSC	0.050 BSC		
Н	0.10	0.25	0.004	0.010	
7	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

#### **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

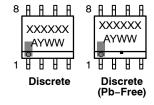
#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location = Wafer Lot

= Year = Work Week

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww

= Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

#### **STYLES ON PAGE 2**

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#### SOIC-8 NB CASE 751-07 ISSUE AK

## DATE 16 FEB 2011

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1  STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE  STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. PINS 2	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1  STYLE 7: PIN 1. IMPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2	3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1  STYLE 12: PIN 1. SOURCE 2. SOURCE
PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND	PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd  STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2	PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1  STYLE 12: PIN 1. SOURCE 2. SOURCE
PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND	PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2	PIN 1. SOURCE 2. SOURCE
6. BIAS 2 7. INPUT 8. GROUND	5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15:  PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		
	PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE 8. CATHODE 8. CATHODE 8. CATHODE 8. CATHODE 9. COMMON CATHODE/VCC 9. COMMON CATHODE/VCC 1. I/O LINE 1 2. COMMON CATHODE/VCC 1. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 5 8. COMMON ANODE/GND 8. COMMON ANODE/GND 8. COMMON ANODE/GND 8. COMMON ANODE/GND 8. I/O LINE 5 8. COMMON ANODE/GND 8. SOURCE 9. II. ILIMIT 9. SOURCE 1. SOURCE 1. SOURCE 1. SOURCE 2. SOURCE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2	PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 7. CATHODE, COMMON 8. N-DRAIN 8. CATHODE, COMMON 8. CATHODE 9IN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 4. GATE 2 5. DRAIN 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1 8. CATHODE 8. CATHODE 8. MIRROR 1 8. COMMON ANODE/GND 8. LINE 1 OUT 8. LINE 2 OUT 9. COMMON ANODE/GND 8. LINE 1 OUT 8. COMMON ANODE/GND 8. LINE 2 OUT 9. COMMON ANODE/GND 9. COMMON ANODE/GND 9. COMMON ANODE/GND 9. COMMON ANODE/GND 9. LINE 2 OUT 9. COMMON ANODE/GND 9. COMMON ANODE/GND 9. LINE 2 OUT 9. COMMON ANODE/GND 9. COMMON ANODE/GND 9. COMMON ANODE/GND 9. COMMON ANODE/GND 9. COMMON ANODE/

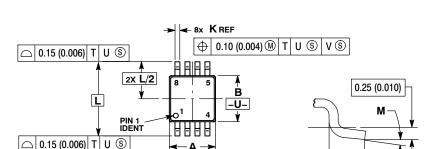
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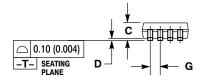
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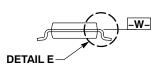
#### **DATE 04/07/2000**



-V-

**DETAIL E** 





- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH. OR GATE BURRS SHALL NOT EXCEED 0.15
- (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
  5. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
  6. DIMENSION A AND B ARE TO BE DETERMINED
- AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.114	0.122
В	2.90	3.10	0.114	0.122
С	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026 BSC	
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193 BSC	
М	0°	6 °	0°	6°

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